

UNISONIC TECHNOLOGIES CO., LTD

BD237

NPN EPITAXIAL SILICON TRANSISTOR

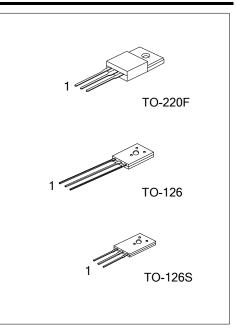
80V, NPN TRANSISTORS

DESCRIPTION

The UTC BD237 is an NPN transistor. it uses UTC's advanced technology to provide customers with high collector-emitter breakdown voltage, etc.

FEATURES

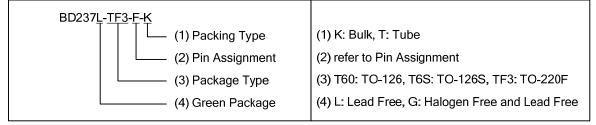
- * Complement to UTC BD238 respectively
- * High collector-emitter breakdown voltage



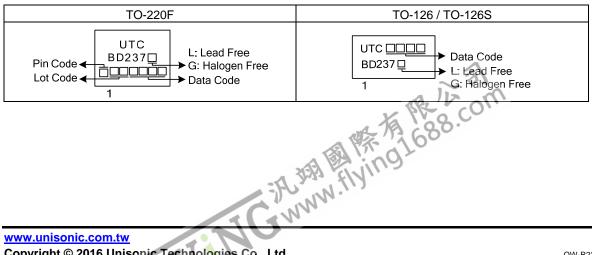
ORDERING INFORMATION

Ordering Number		Bookogo	Pin Assignment			Dooking	
Lead Free	Halogen Free	- Package	1	2	3	Packing	
BD237L-T60-K	BD237G-T60-K	TO-126	Е	С	В	Bulk	
BD237L-T6S-K	BD237G-T6S-K	TO-126S	Е	С	В	Bulk	
BD237L-TF3-T	BD237G-TF3-T	TO-220F	Е	С	В	Tube	
BD237L-TF3-F-T	BD237G-TF3-F-T	TO-220F	В	С	Е	Tube	
Note: Pin assignment: E: Emitter B: Base C: Collector							

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MARKING



■ **ABSOLUTE MAXIMUM RATINGS** (T_A=25°C, unless otherwise noted)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage		V _{CBO}	100	V
Collector-Emitter Voltage		V _{CEO}	80	V
Emitter-Base Voltage		V _{EBO}	5	V
Continuous Collector Current		I _C	2	А
Collector Dissipation	TO-126/ TO-126S	6	1.25	W
	TO-220F	Pc	1.6	W
Junction Temperature		ΤJ	+150	°C
Storage Temperature Range		T _{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

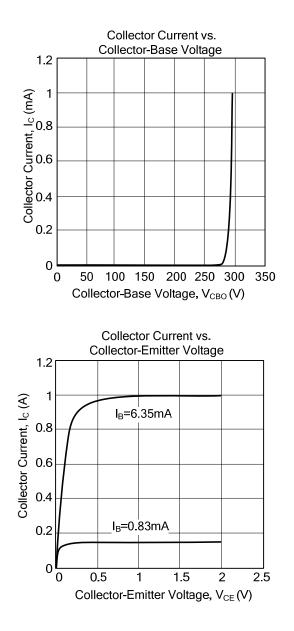
■ ELECTRICAL CHARACTERISTICS (T_A =25°C, unless otherwise specified)

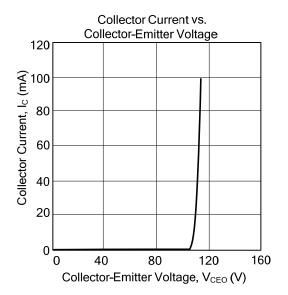
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	$I_{C}=1mA$, $I_{E}=0$	100			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =100mA, I _B =0	80			V
Emitter-Base Breakdown Voltage	BV _{EBO}	$I_E=1mA$, $I_C=0$	5			V
Collector Cut-Off Current	I _{CBO}	V _{CB} =100V, I _E =0			100	μA
Emitter Cut-Off Current	I _{EBO}	$V_{EB}=5V, I_{C}=0$			1	mA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =1A, I _B =100mA			0.6	V
DC Current Gain	h _{FE} (1)	I _C =150mA,V _{CE} =2V	40			
	h _{FE} (2)	I _C =1A,V _{CE} =2V	25			
Transition Frequency	f⊤	I _C =250mA, V _{CE} =10V, f=10MHz	3			MHz



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TYPICAL CHARACTERISTICS





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